

EE 508

Lecture 27

Nonideal Effects in Switched Capacitor Circuits

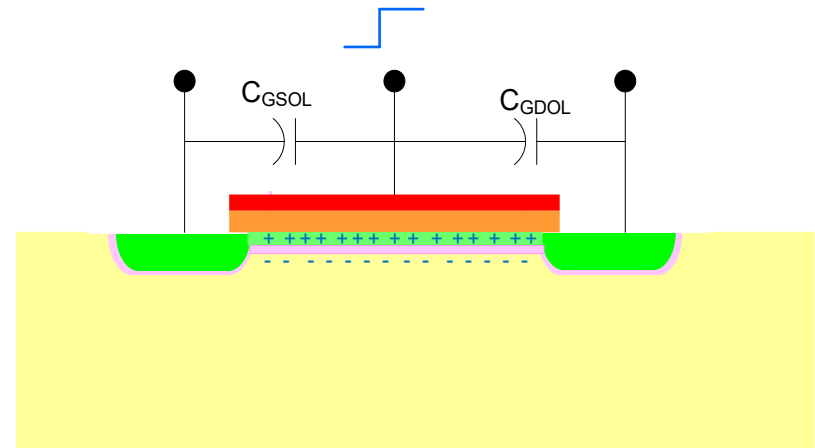
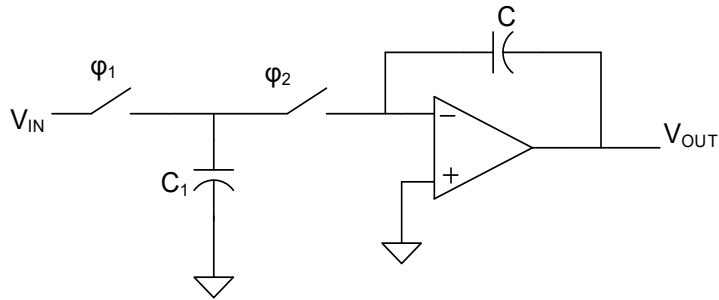
Noise

Switched-Resistor Filters

Other Integrators

Review from Last Lecture

Charge Injection

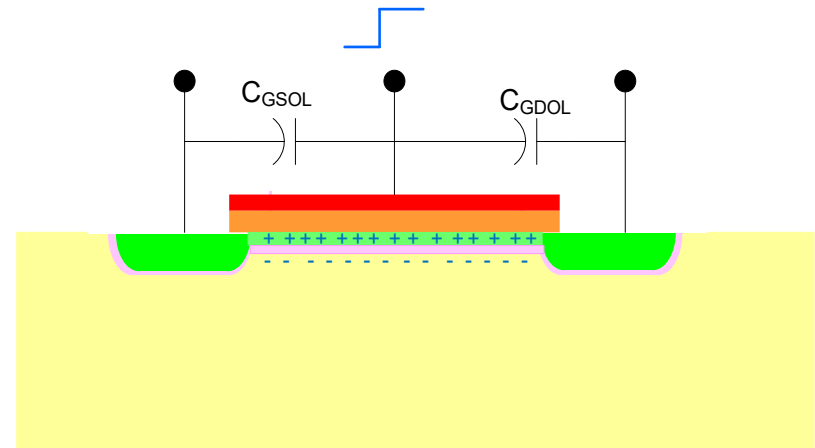
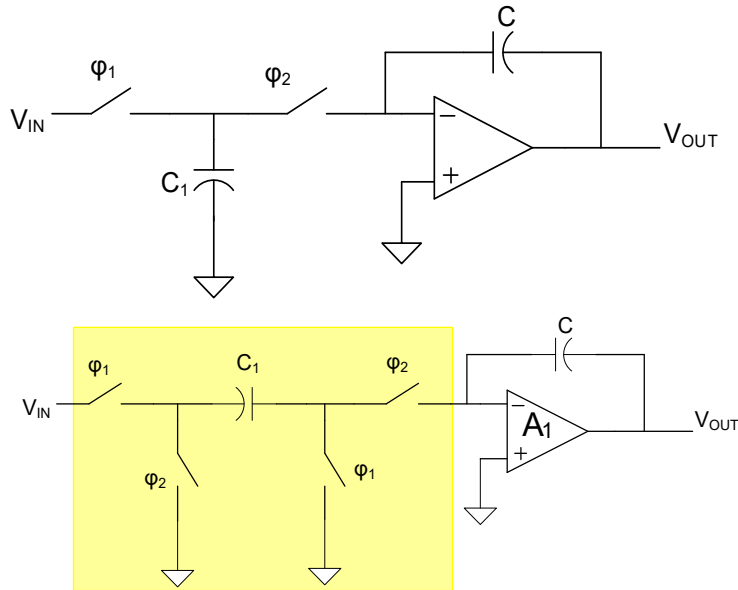


n-channel MOSFET

- If Φ_1 opens slowly, channel charge will all exit through V_{IN}
- If Φ_1 opens quickly, some charge will exit to left and some to right and split depends upon impedances seen to left and right
- Often not practical to open switches slowly
- Channel charge injection introduces errors in charge transfer and affects linearity

Review from Last Lecture

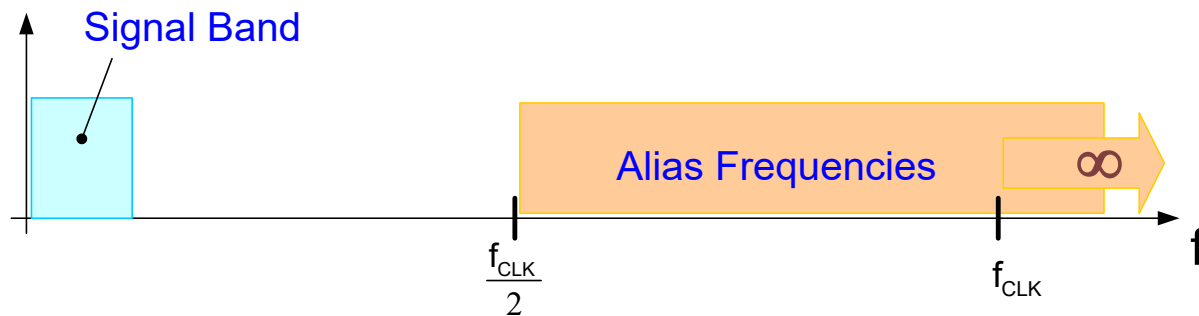
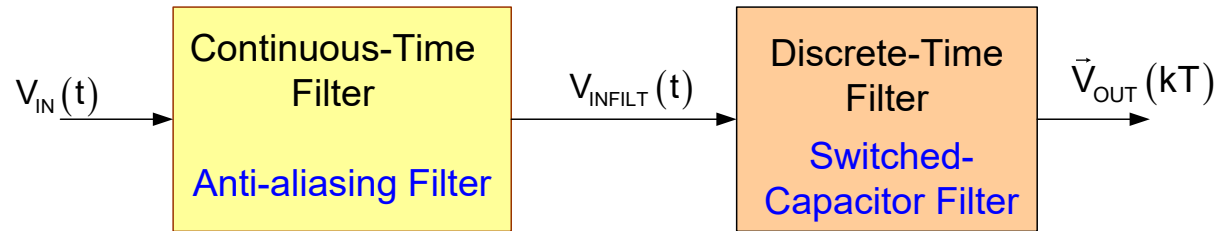
Charge Injection



n-channel MOSFET

- Somewhat more complicated in multi-switch implementations
- There will naturally be a small amount of skew on clocks and this skew will affect charge injection
- Charge injection from some switches can be reduced or eliminated by using advanced clock (e.g. lower Φ_1 switch opens before upper Φ_1 switch)

Anti-aliasing filter often required to limit frequency content at input to SC filters



Why not just make the clock frequency \gg signal band edge ?

Recall in the continuous-time RC-SC counterparts

$$f_{POLES} \cong \frac{1}{RC} \cong f_{CLK} \frac{C_1}{C}$$

Since f_{POLES} will be in the signal band (that is why we are building a filter) large f_{CLK} will require large capacitor ratios if $f_{CLK} \gg f_{POLES}$

- Large capacitor ratios not attractive on silicon (area and matching issues)
- High f_{CLK} creates need for high GB in the op amps (area, power, and noise increase)

Often f_{CLK}/f_{POLES} in the 10:1 range proves useful (20:1 to 5:1 typical)

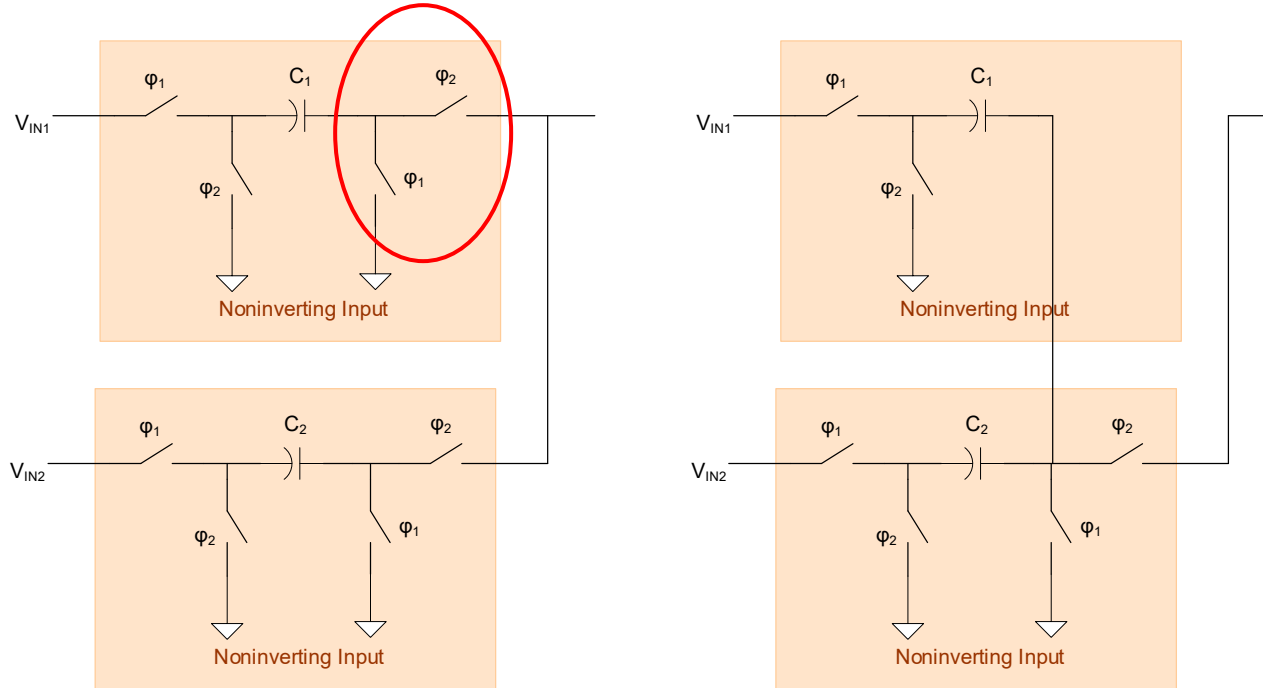
Nonideal Effects in Switched Capacitor Circuits

- Parasitic Capacitances
- Charge Injection
- Aliasing
- • Redundant Switch Removal
- Matching
- Noise

Review from Last Lecture

Elimination of Redundant Switches

Redundant Switches



Switched-Capacitor Input
with Redundant Switches

Switched-Capacitor Input with
Redundant Switches Removed

Although developed from the concept of SC-resistor equivalence, SC circuits often have no Resistor-Capacitor equivalents

Nonideal Effects in Switched Capacitor Circuits

- Parasitic Capacitances
- Charge Injection
- Aliasing
- Redundant Switch Removal
- Matching
- Noise

Review from Last Lecture

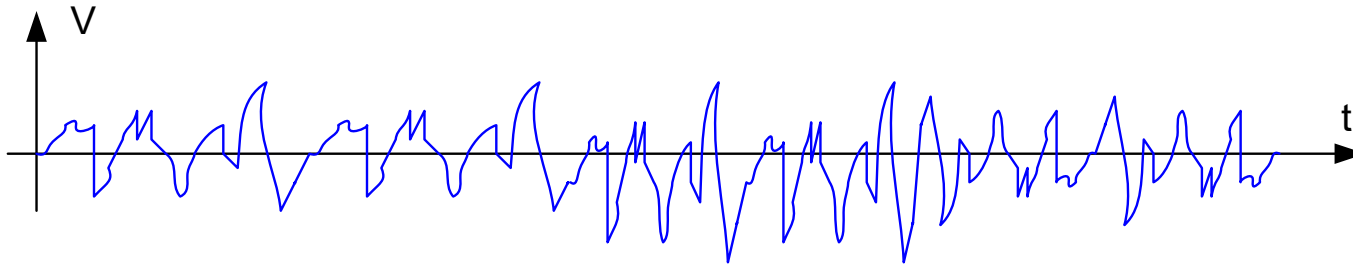
Matching

- Matching is a statistical concept and directly relates to yield
- With good layout, matching to 0.01% or better can be achieved
- Common-centroid widely used to eliminate gradient effects
- Pelgrom parameter useful for analytically predicting yield with common-centroid layouts
- Area affects local variations
- Little in the literature or in PDKs to predict matching without gradient cancellation
- Must match all contacts and interconnects to get good matching
- Neighbor effects are important

Nonideal Effects in Switched Capacitor Circuits

- Parasitic Capacitances
- Op Amp Affects
- Charge Injection
- Aliasing
- Redundant Switch Removal
- Matching
- • Noise

Noise in Continuous-time Linear Systems



Noise in continuous-time systems

$$v_{RMS} = \sqrt{\lim_{T_x \rightarrow \infty} \left(\frac{1}{T_x} \int_0^{T_x} v_n^2(t) dt \right)}$$

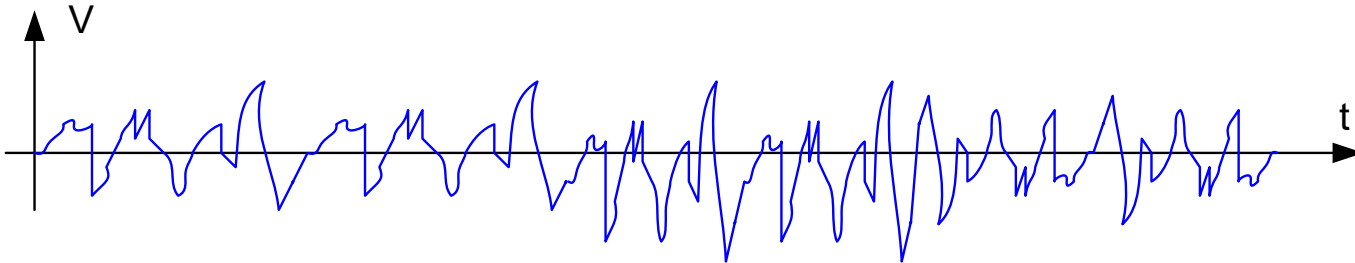
$\int_0^{T_x} v_n^2(t) dt$ is a random variable

At the design phase, we do not know what the time-domain noise characteristics will be

$$v_{RMS} = E \left(\sqrt{\lim_{T \rightarrow \infty} \left(\frac{1}{T} \int_0^T V^2(t) dt \right)} \right)$$

E denotes the expected value of the random variable

Noise in Continuous-Time Linear Systems



Noise often characterized by the spectral density S

$$v_{RMS} = \sqrt{\int_0^{\infty} S(f) df}$$

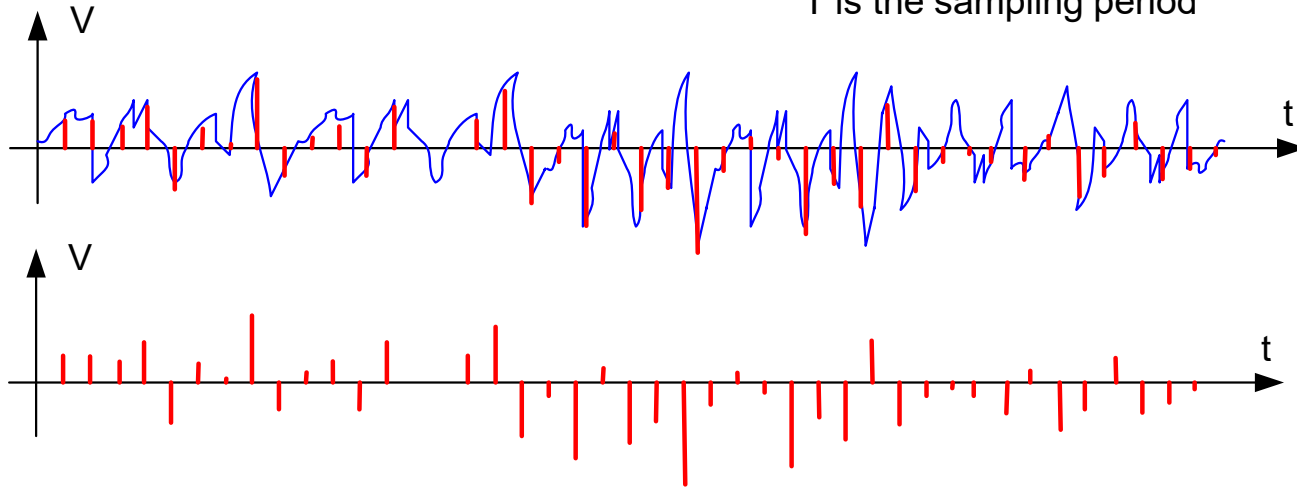
$$\int_{f=0}^{\infty} S(f) df = \lim_{f_x \rightarrow \infty} \int_{f=0}^{f_x} S(f) df$$

Thus

$$\sqrt{\lim_{T_x \rightarrow \infty} \left(\frac{1}{T_x} \int_0^{T_x} v_n^2(t) dt \right)} = \sqrt{\int_0^{\infty} S(f) df} = \sqrt{\lim_{f_x \rightarrow \infty} \int_{f=0}^{f_x} S(f) df}$$

Relation between continuous-time and discrete-time noise

Assume $v_n(t)$ is a continuous-time noise source
 T is the sampling period



Noise in discrete-time linear systems

$$\vec{V}(kT) = \langle v_n(mT) \rangle_{m=0}^{\infty}$$

$$\vec{V}_{RMS} = \sqrt{\lim_{M \rightarrow \infty} \left(\frac{1}{M} \sum_{k=0}^M v_n^2(kT) \right)}$$

$$\sigma(v_n(kT)) = v_{RMS}$$

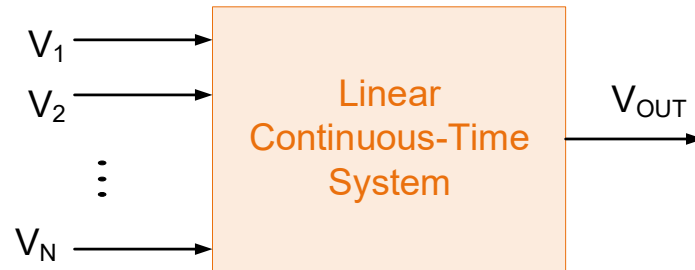
Noise in continuous-time linear systems

$$v_{RMS} = E \left(\sqrt{\lim_{T \rightarrow \infty} \left(\frac{1}{T} \int_0^T V^2(t) dt \right)} \right)$$

Noise in discrete-time system is identical to that of the continuous-time system

$$\vec{V}_{RMS} = v_{RMS}$$

Noise Summing in continuous-time Linear Systems



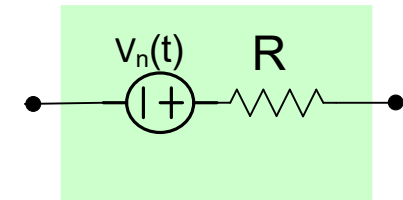
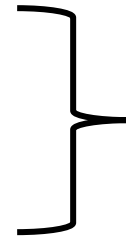
$$V_{OUT}(s) = \sum_{i=1}^N T_i(s) V_i(s)$$

$$S_{OUT} = \sum_{i=1}^N S_i \cdot |T_i(j\omega)|^2$$

$$v_{OUT_RMS} = \sqrt{\int_{f=0}^{\infty} S_{OUT} df} = \sqrt{\int_{f=0}^{\infty} \sum_{i=1}^N S_i \cdot |T_i(j\omega)|^2 df}$$

Noise

- Capacitors do not contribute any noise
- Resistors contribute thermal noise
- Switches contribute thermal noise



Noise model of any resistor
 $V_n(t)$ dependent on value of R

$$S_{V_n} = 4kTR$$

- Noise due to switches looks like “capacitive” noise

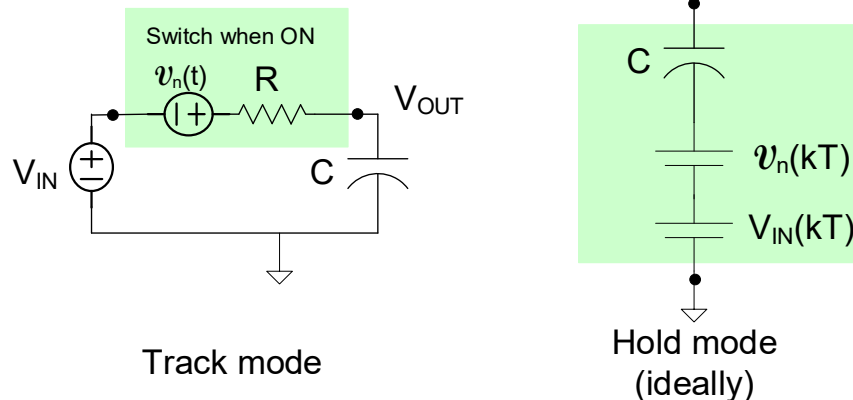
$$V_{RMS} = \sqrt{\frac{kT}{C}}$$

Noise in switched capacitor circuits

- Noise due to switches looks like “capacitive” noise

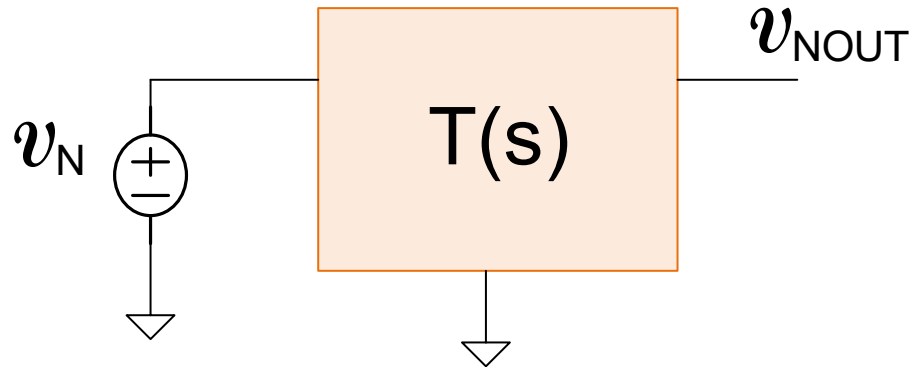
$$V_{RMS} = \sqrt{\frac{kT}{C}}$$

Consider a capacitor that is sampling an input signal V_{IN}



Neither the noise voltage nor the input voltage sampled onto C will be ideal if R is not near 0Ω

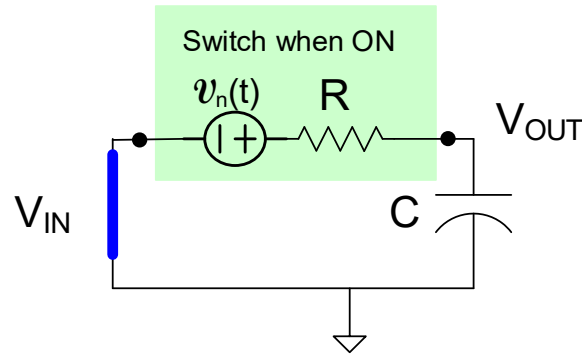
Noise review



Component of spectral density at output due to any noise source with spectral density S_x given by

$$S(\omega) = S_x |T(j\omega)|^2$$

Noise during sampling phase



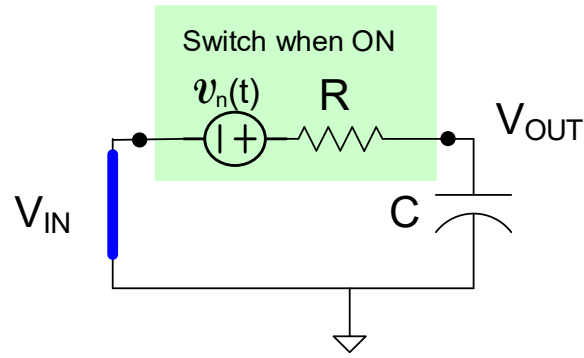
$$S(\omega) = S_x |T(j\omega)|^2$$

$$T(s) = \frac{1}{1 + RCs}$$

$$S_{v_n} = 4kTR$$

$$S_{v_{OUT}} = 4kTR \left(\frac{1}{1 + (RC\omega)^2} \right)$$

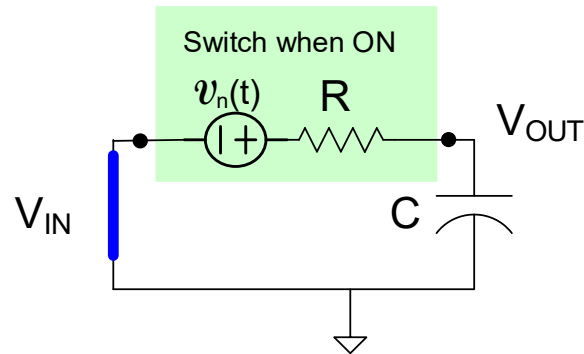
Noise during sampling phase



$$S_{V_{OUT}} = 4kTR \left(\frac{1}{1 + (RC\omega)^2} \right)$$

$$v_{n_{RMS}} = \sqrt{\int_{f=0}^{\infty} S_{V_{OUT}} df} = \sqrt{\int_{f=0}^{\infty} \frac{4kTR}{1 + \omega^2 R^2 C^2} df}$$

Noise during sampling phase

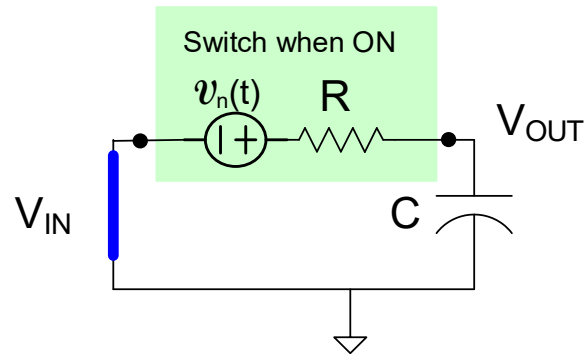


$$v_{n_{RMS}} = \sqrt{\int_{f=0}^{\infty} S_{V_{OUT}} df} = \sqrt{\int_{f=0}^{\infty} \frac{4kTR}{1 + \omega^2 R^2 C^2} df}$$

It can be shown that this integral is independent of R and is given by

$$v_{n_{RMS}} = \sqrt{\int_{f=0}^{\infty} S_{V_{OUT}} df} = \sqrt{\frac{kT}{C}}$$

Noise during sampling phase



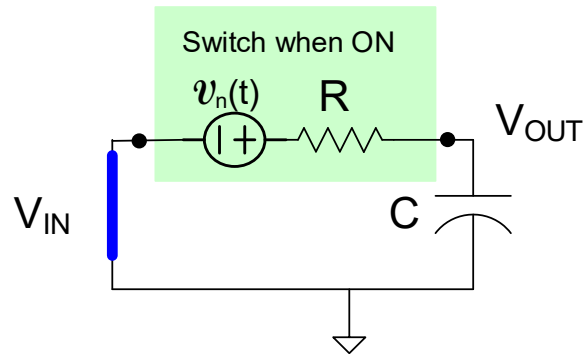
$$v_{n_{RMS}} = \sqrt{\frac{kT}{C}}$$

RMS noise voltage on C is independent of the state of the switch

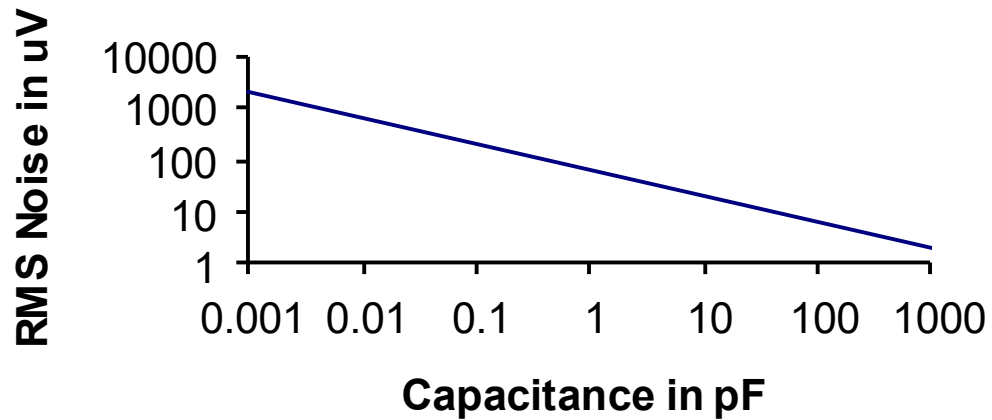
So sampled RMS noise voltage should be same as instantaneous RMS voltage

Highly temperature dependent

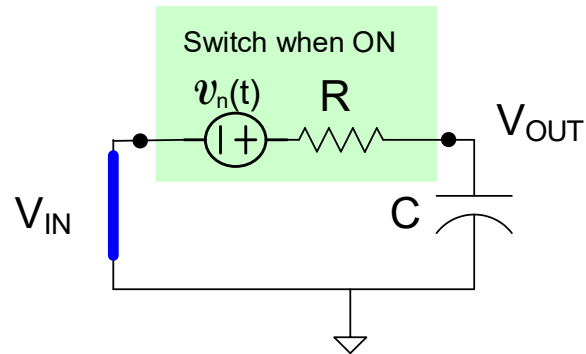
Noise during sampling phase



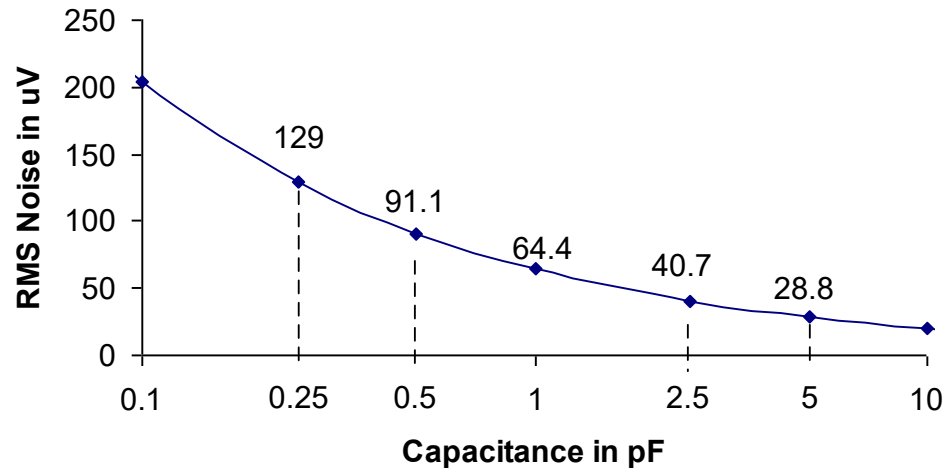
"kT/C" Noise at T=300K



Noise during sampling phase



"kT/C" Noise at T=300K



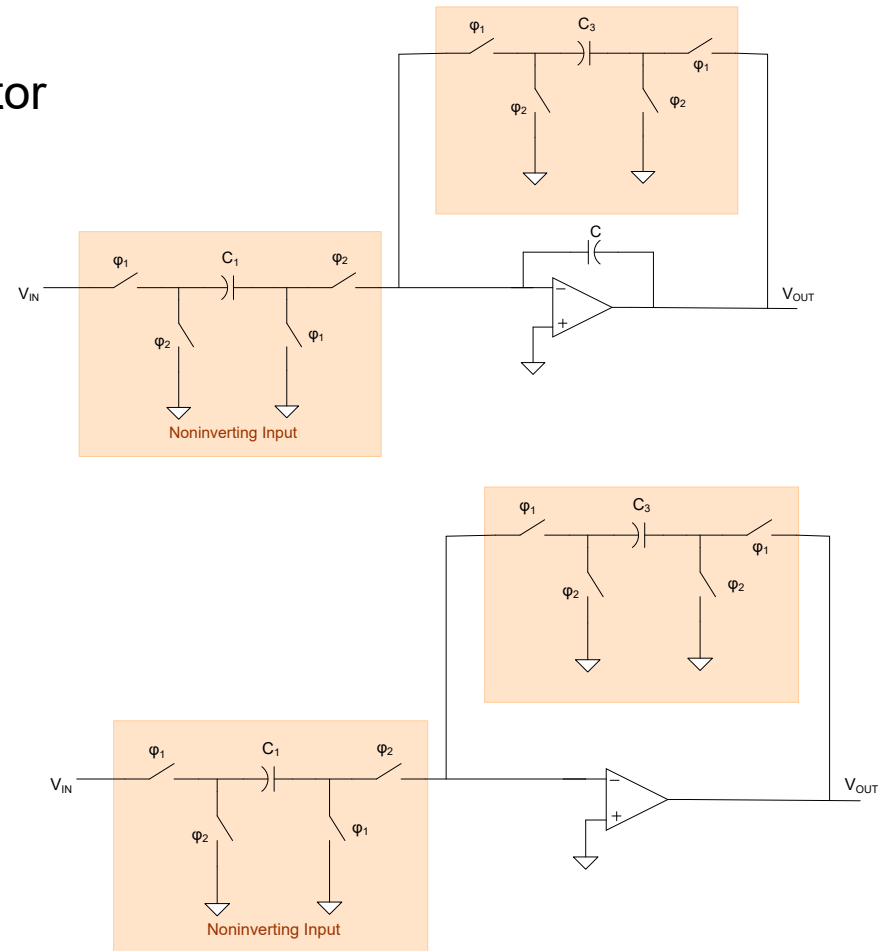
Noise

- Capacitors do not have any noise source
- Switches contribute thermal noise
- Noise due to switches looks like “capacitive” noise $V_{RMS} = \sqrt{\frac{kT}{C}}$

Be careful with calculating noise in SC circuits !

Switched Capacitor Amplifiers

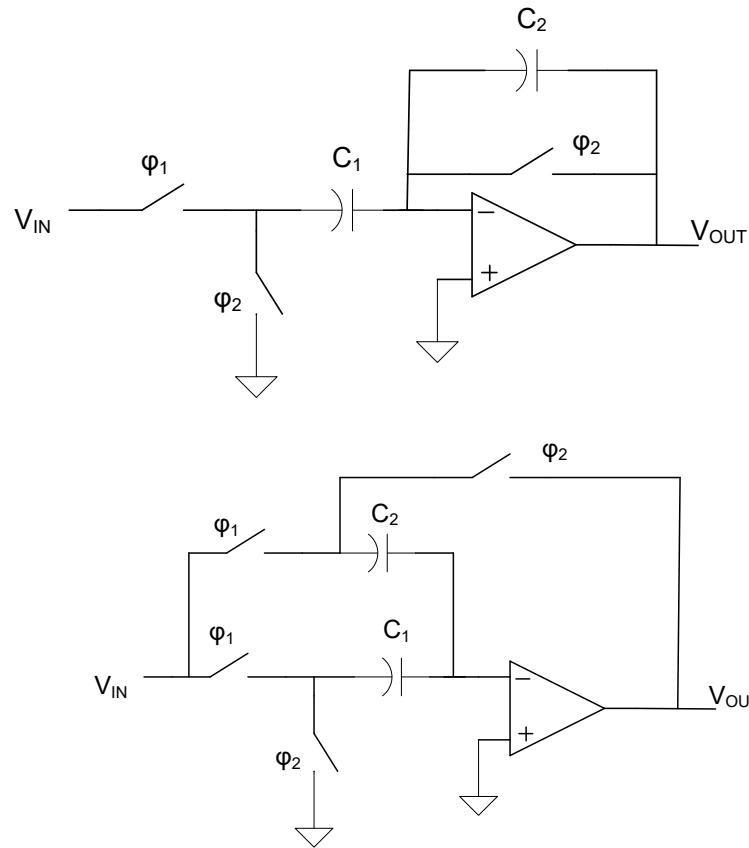
Elimination of the Integration Capacitor



What happens if the integration capacitor is eliminated?

- Serves as a SC amplifier with gain of $A_V = C_1/C_2$
- SC amplifiers and SC summing amplifiers are widely used in filter and non-filter applications

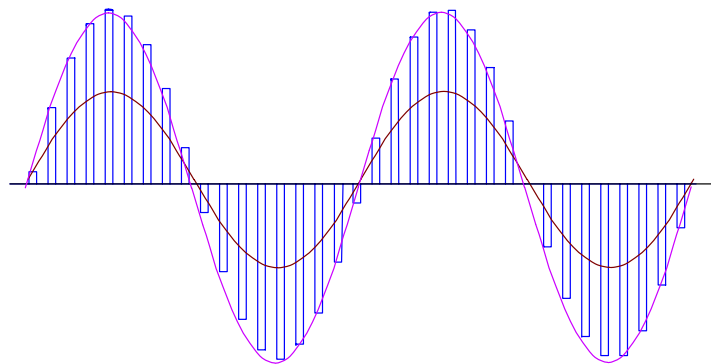
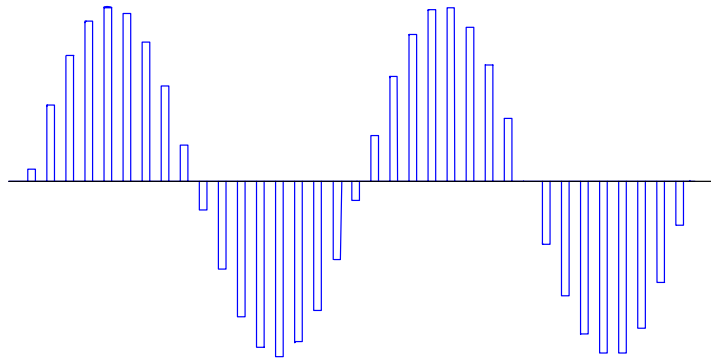
Switched Capacitor Amplifiers



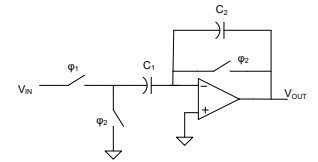
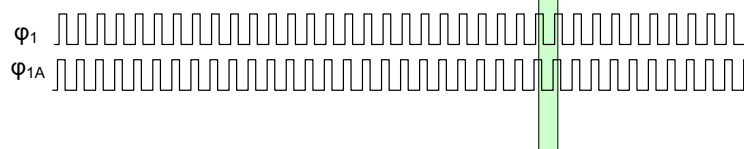
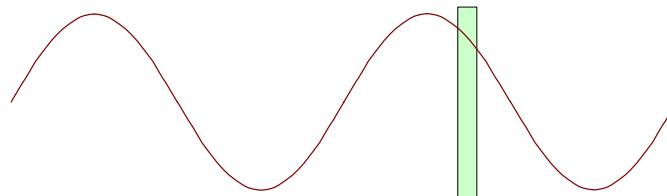
- Summing, Differencing, Inverting, and Noninverting SC Amplifiers Widely Used
- Significant reduction in switches from what we started with by eliminating C in SC integrator
- Must be stray insensitive in most applications
- Outputs valid only during one phase

Switched Capacitor Amplifiers

Output



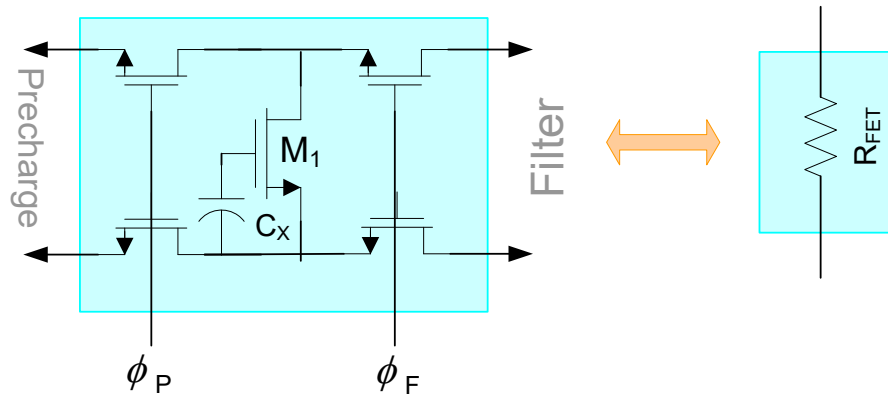
Input



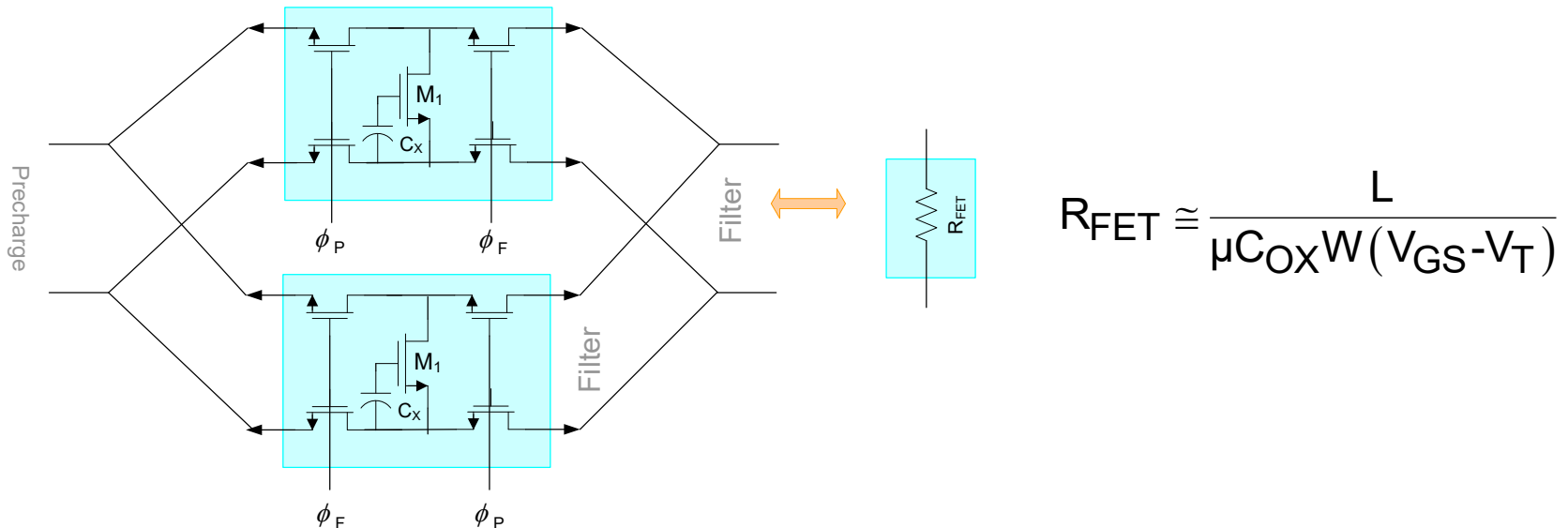
Voltage Mode Integrators

- Active RC (Feedback-based)
 - MOSFET-C (Feedback-based)
 - OTA-C
 - TA-C
 - Switched Capacitor
 - Switched Resistor
 - Other Structures
- Sometimes termed “current mode”
- Will discuss later

Switched-Resistor Voltage Mode Integrators

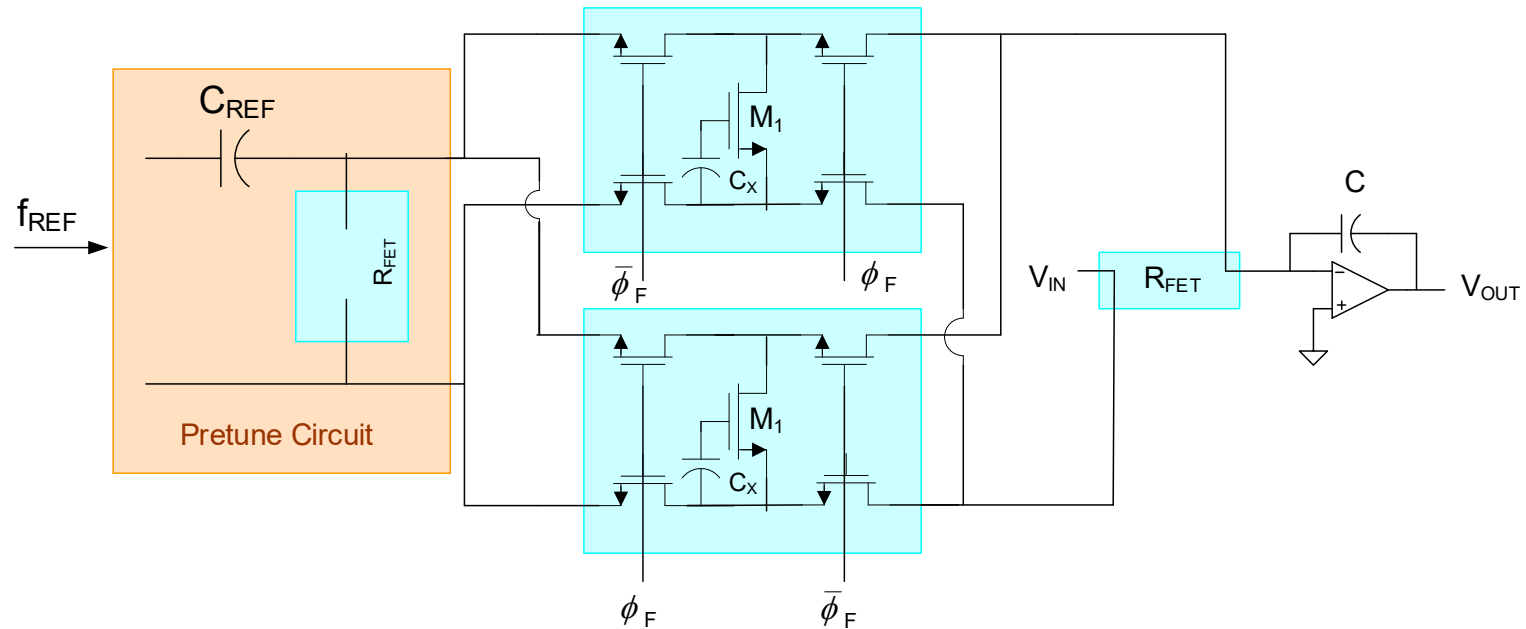


Observe that if a triode-region MOS device is switched between a precharge circuit and a filter circuit (or integrator) and V_{GS} is held constant, It will behave as a resistor while in the filter circuit



Observe that if two such circuits are switched between a precharge circuit and a filter circuit (or integrator) and V_{GS} is held constant, it will behave as a resistor in the filter circuit at all times

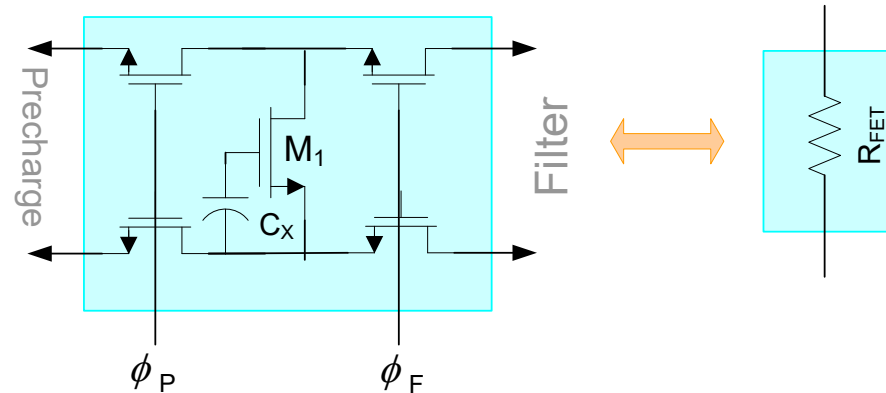
Switched-Resistor Voltage Mode Integrators



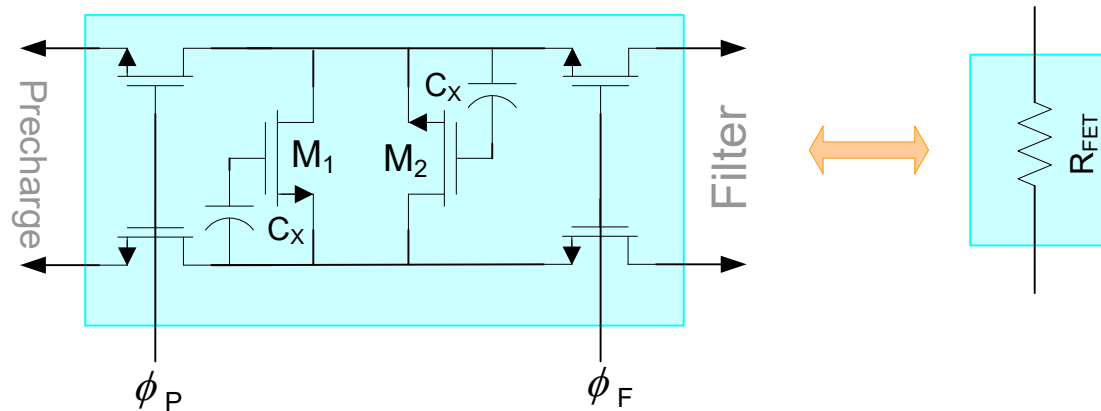
Switched-resistor integrator

- Clock frequency need only be fast enough to prevent droop on C_X
- Minor overlap or non-overlap of clock plays minimal role in integrator performance
- Switched-resistors can be used for integrator resistor or to replace all resistors in any filter
- Pretune circuit can accurately establish $R_{FET} C_{REF}$ product proportional to f_{REF}
- $R_{FET} C$ product is given by $R_{FET} C = R_{FET} C \frac{C_{REF}}{C_{REF}} = [R_{FET} C_{REF}] \cdot \left[\frac{C}{C_{REF}} \right]$ and is thus accurately controlled

Switched-Resistor Voltage Mode Integrators

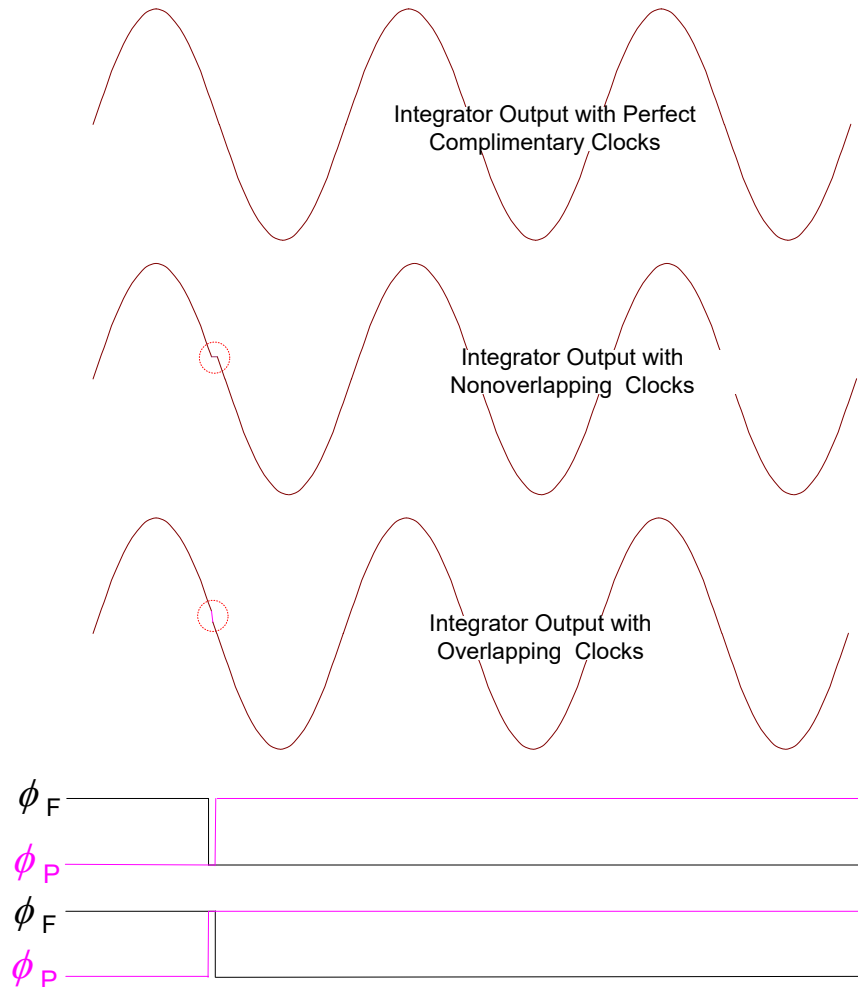


There are some modest nonlinearities in this MOSFET when operating in the triode region



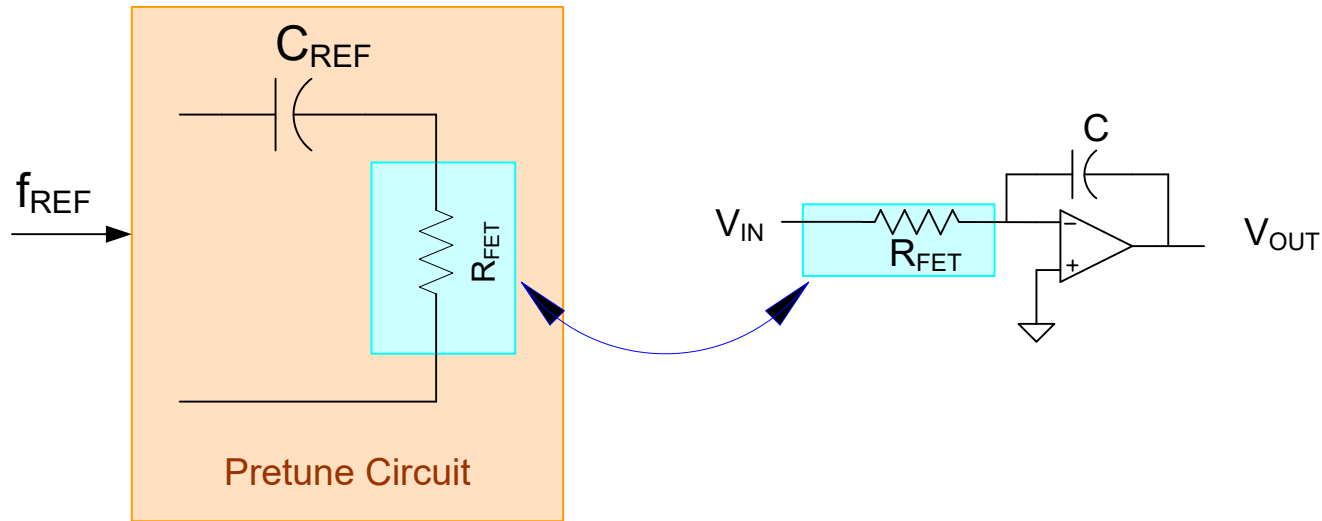
- Significant improvement in linearity by cross-coupling a pair of triode region resistors
- Perfectly cancels nonlinearities if square law model is valid for M_1 and M_2
- Only modest additional complexity in the Precharge circuit

Switched-Resistor Voltage Mode Integrators



- Aberrations are very small, occur very infrequently, and are further filtered
- Play almost no role on performance of integrator or filter

Switched-Resistor Voltage Mode Integrators



Switched-resistor integrator

- Accurate CR_{FET} products is possible
- Area reduced compared to Active RC structure because R_{FET} small
- Single pretune circuit can be used to “calibrate” large number of resistors
- Clock frequency not fast and not critical (but accuracy of f_{REF} is important)
- Since resistors are memoryless elements, no transients associated with switching
- Since filter is a feedback structure, speed limited by BW of op amp

Voltage Mode Integrators

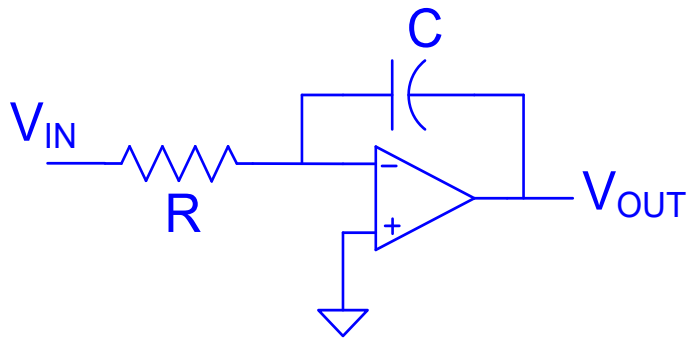
- Active RC (Feedback-based)
 - MOSFET-C (Feedback-based)
 - OTA-C
 - TA-C
 - Switched Capacitor (Feedback-based)
 - Switched Resistor (Feedback-based)
 - Other Structures
- Sometimes termed “current mode”
- Discrete Time

Have introduced a basic voltage-mode integrators in each of these approaches

All of these structures have applications where they are useful

Performance of feedback-based structures limited by Op Amp BW

Variants of basic inverting integrator have been considered



Basic Miller Integrator

- Active RC
- MOSFET-C
- OTA-C
- g_m -C
- Switched-Capacitor
- Switched-Resistor

Performance of all is limited by GB of Operational Amplifiers

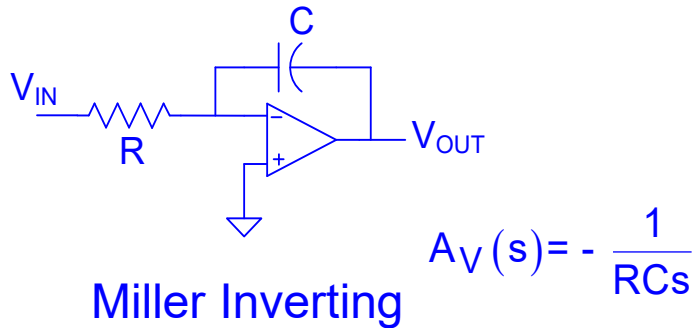
How can integrator performance be improved?

- Better op amps
- Better Integrator Architectures

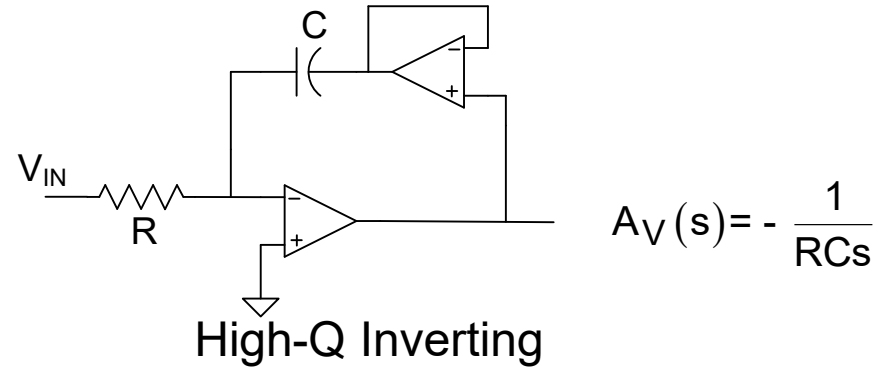
How can the performance of integrator structures be compared?

Need metric for comparing integrator performance

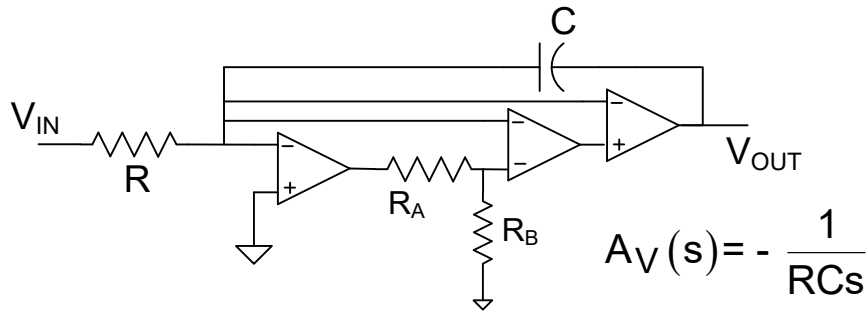
Are there other integrators in the basic classes that have been considered?



$$A_V(s) = -\frac{1}{RCs}$$

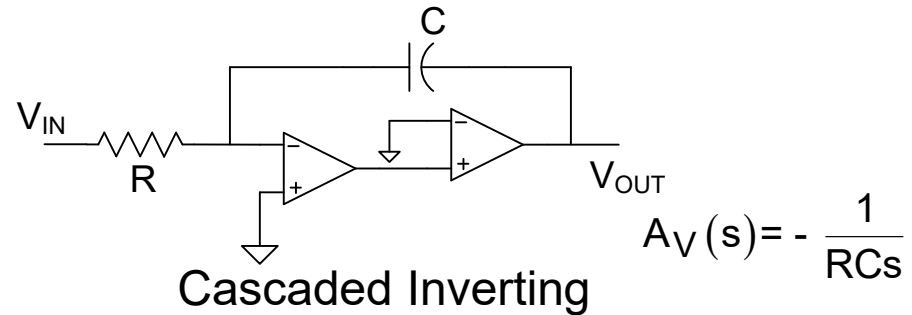


$$A_V(s) = -\frac{1}{RCs}$$



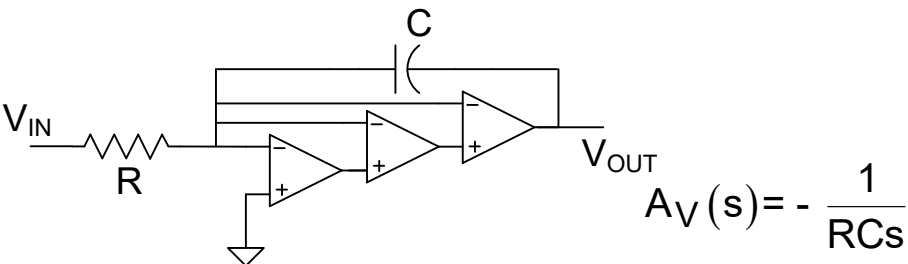
$$A_V(s) = -\frac{1}{RCs}$$

Zero Second Derivative Inverting



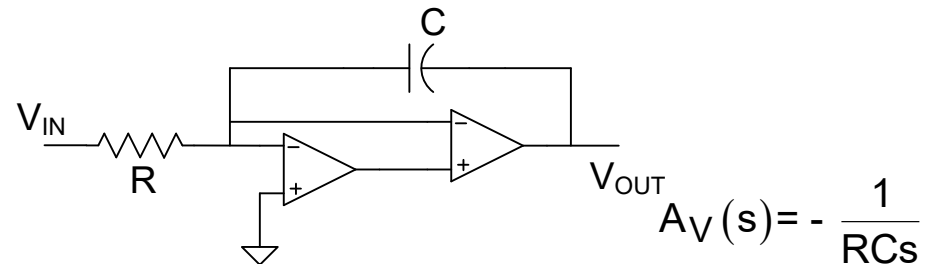
$$A_V(s) = -\frac{1}{RCs}$$

Cascaded Inverting



$$A_V(s) = -\frac{1}{RCs}$$

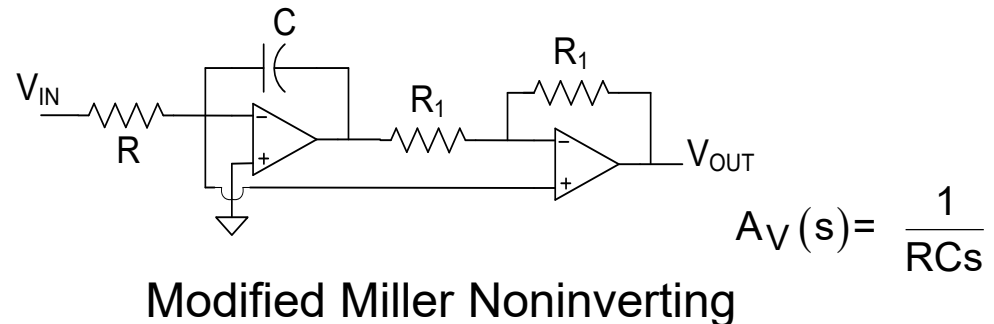
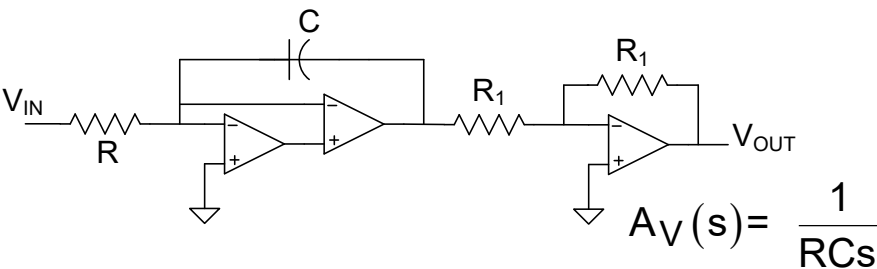
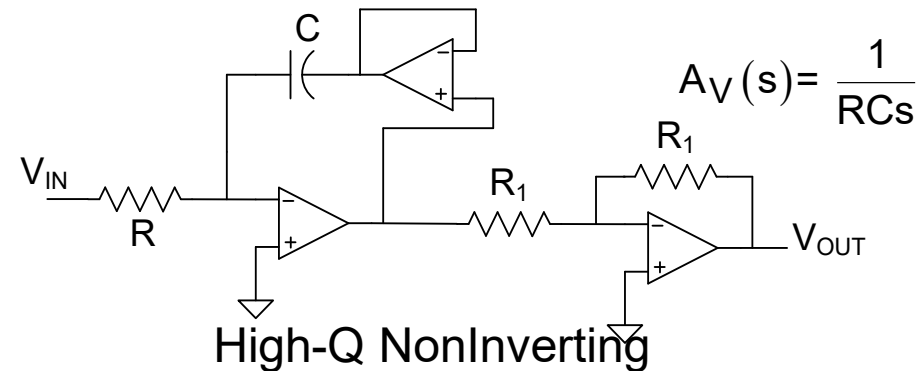
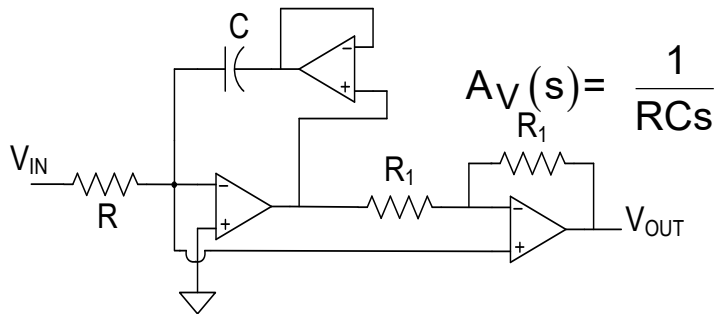
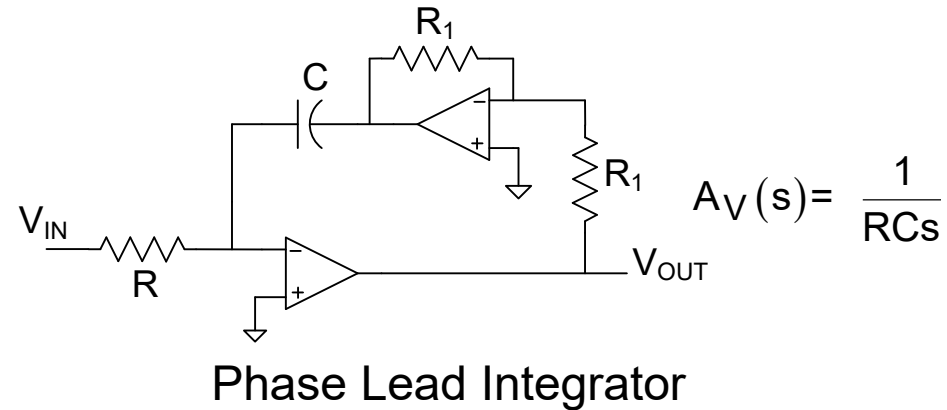
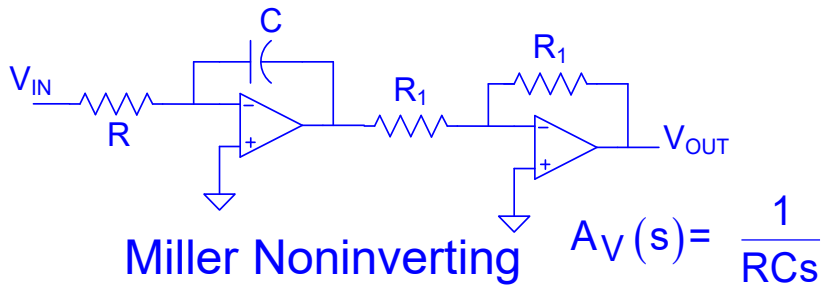
Zero Second Derivative Inverting



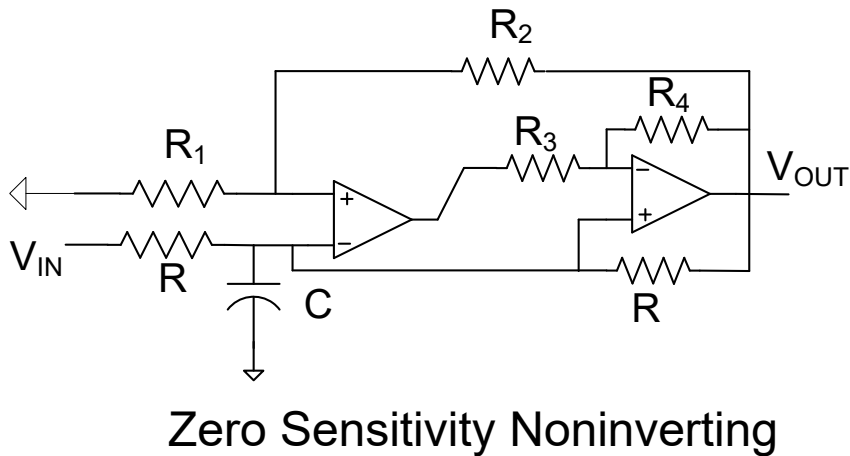
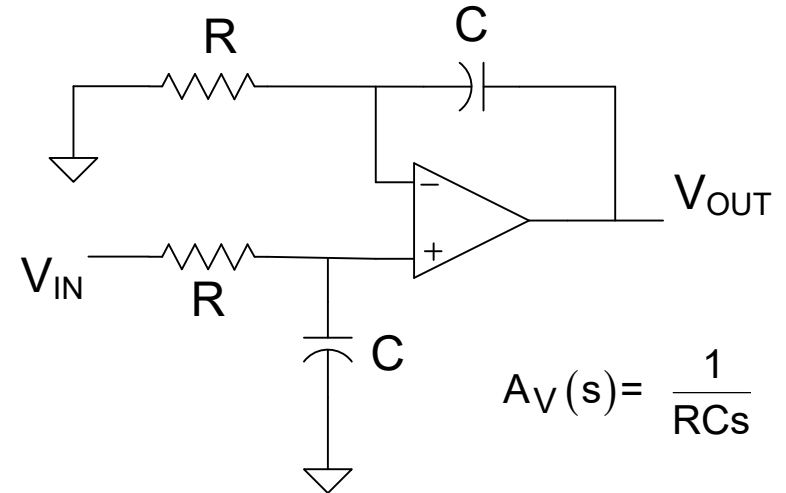
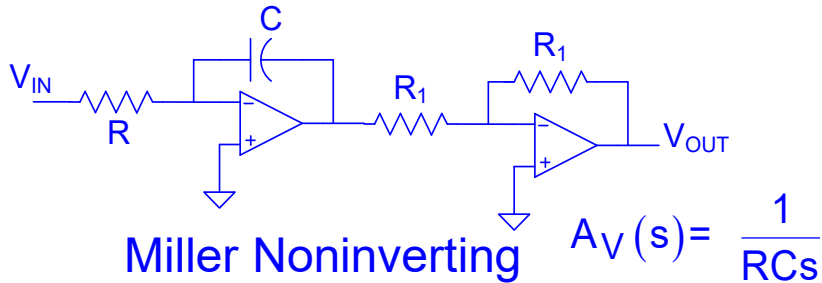
$$A_V(s) = -\frac{1}{RCs}$$

Zero Sensitivity Inverting

Are there other integrators in the basic classes that have been considered?



Are there other integrators in the basic classes that have been considered?



$$A_V(s) = \frac{2}{RCs}$$

If $R_1=R_2$ and $R_3=R_4$

(note this has a grounded integrating capacitor!)



Stay Safe and Stay Healthy !

End of Lecture 27